60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE *INTELLIFET*® MOSFET

Product Summary

- Continuos Drain-Source Voltage: 60V
- On-State Resistance: 500mΩ
- Nominal Load Current (V_{IN} = 5V): 1.3A
- Clamping Energy: 120mJ

Description

The ZXMS6004DN8 is a dual self-protected low side MOSFET with logic level input. It integrates over-temperature, overcurrent, overvoltage (active clamp) and ESD protected logic level functionality. The ZXMS6004DN8 is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Lamp Driver
- Motor Driver
- Relay Driver
- Solenoid Driver

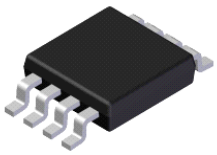
Features and Benefits

- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Overvoltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- High Continuous Current Rating
- **Totally Lead-Free; RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

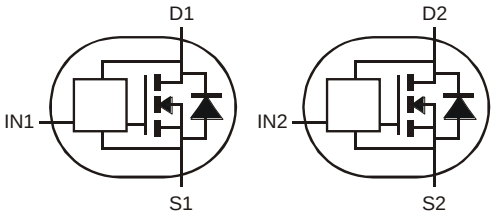
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish e3
- Weight: 79.1 mg (Approximate)

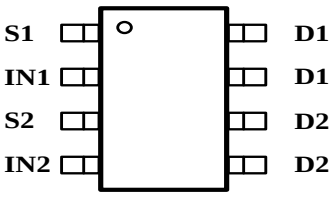
SO-8



Top View



Device Symbol



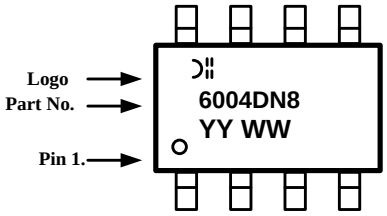
Top View
Pin-Out

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMS6004DN8-13	6004DN8	13	12	2,500 units

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Top View

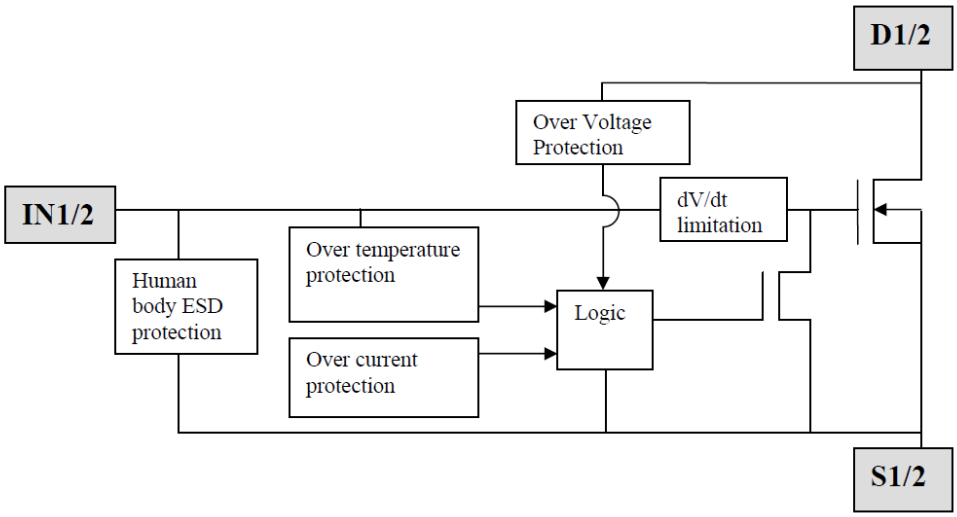
6004DN8 = Product name

YY: Year
WW: Week: 01~52;
52 represents 52 and 53 week

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Functional Block Diagram



Application Information

- Two completely isolated independent channels
- Especially suited for loads with a high in-rush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- µC compatible power switch for 12V and 24V DC applications
- Replaces electromechanical relays and discrete circuits
- Linear Mode Capability — the current-limiting protection circuitry is designed to deactivate at low V_{DS} to minimize on-state power dissipation The maximum DC operating current is therefore determined by the thermal capability of the package or board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low V_{DS}

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Units
Continuous Drain-Source Voltage	V_{DS}	60	V
Drain-Source Voltage For Short Circuit Protection	$V_{DS(SC)}$	36	V
Continuous Input Voltage	V_{IN}	-0.5 to +6	V
Continuous Input Current @ -0.2V ≤ V_{IN} ≤ 6V Continuous Input Current @V_{IN} < -0.2V or V_{IN} > 6V	I_{IN}	No limit $\lvert I_{IN} \rvert$ ≤2	mA
Pulsed Drain Current @V_{IN} = 3.3V	I_{DM}	2	A
Pulsed Drain Current @V_{IN} = 5V	I_{DM}	2.5	A
Continuous Source Current (Body Diode) (Note 5)	I_S	1	A
Pulsed Source Current (Body Diode)	I_{SM}	5	A
Unclamped Single Pulse Inductive Energy, T_J = +25°C, I_D = 0.5A, V_{DD} = 24V	E_{AS}	120	mJ
Electrostatic Discharge (Human Body Model)	V_{HBM}	4,000	V
Charged Device Model	V_{CDM}	1,000	V

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Thermal Characteristics

Characteristic	Symbol	Value	Units
Power Dissipation at T_{amb} = +25°C (Note 5) Linear Derating Factor	P_D	1.21 9.7	W mW/°C
Power Dissipation at T_{amb} = +25°C (Note 6) Linear Derating Factor	P_D	1.56 12.5	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	103	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	81	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	13.5	°C/W
Operating Temperature Range	T_J	-40 to +150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
7. Thermal resistance between junction and the mounting surfaces of drain and source pins.

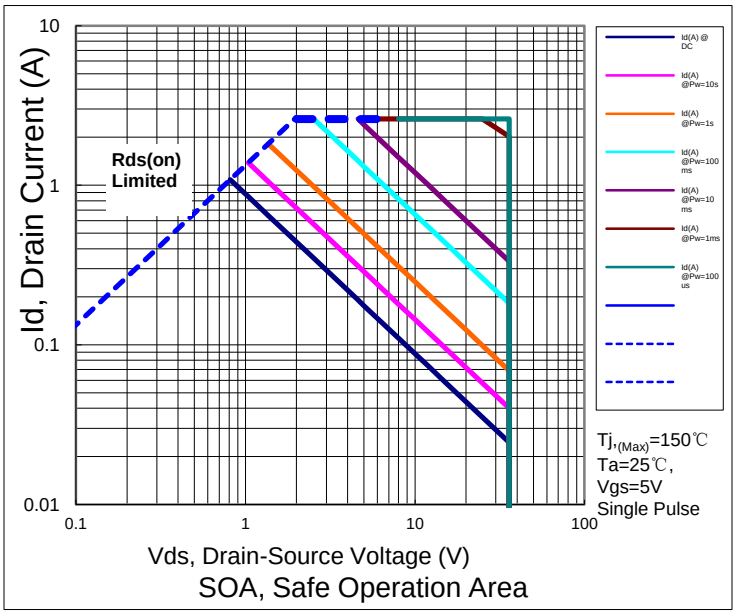
Recommended Operating Conditions

The ZXMS6004DN8 is optimized for use with µC operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V_{IN}	0	5.5	V
Ambient Temperature Range	T_A	-40	+125	°C
High Level Input Voltage for MOSFET to be On	V_{IH}	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	V_{IL}	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	V_P	0	36	V

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Thermal Characteristics (Continued)



SOA, Safe Operation Area

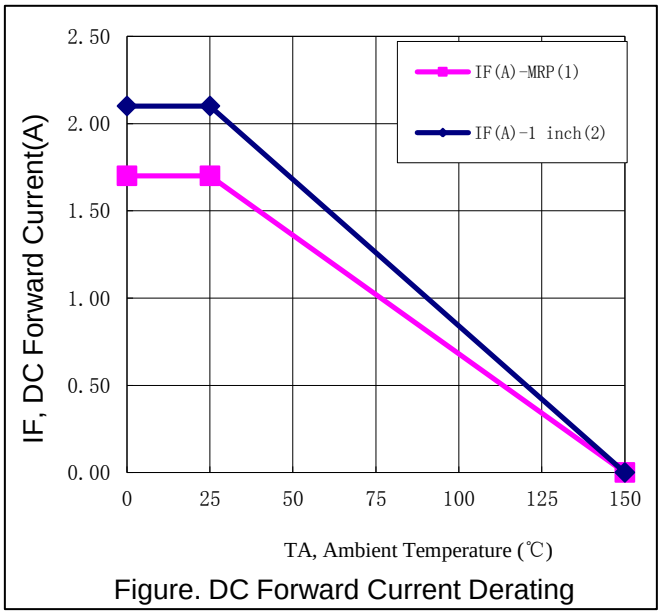


Figure. DC Forward Current Derating

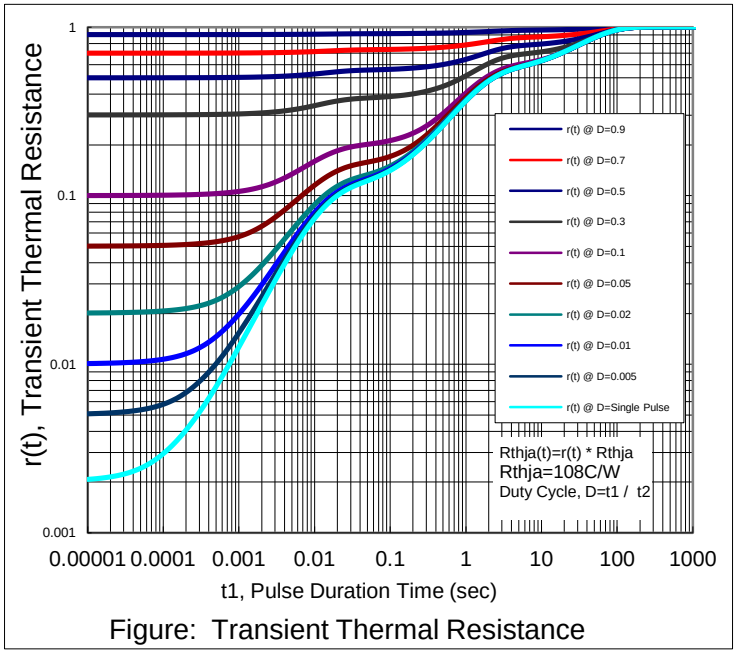


Figure: Transient Thermal Resistance

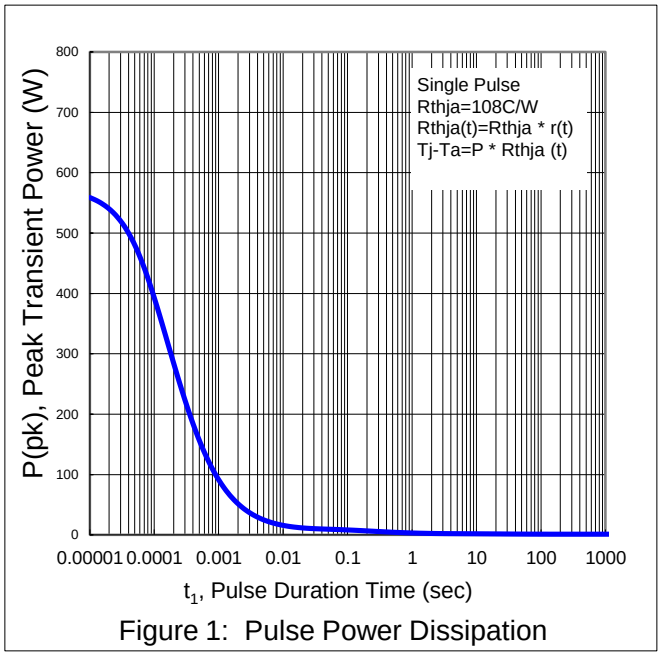


Figure 1: Pulse Power Dissipation

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

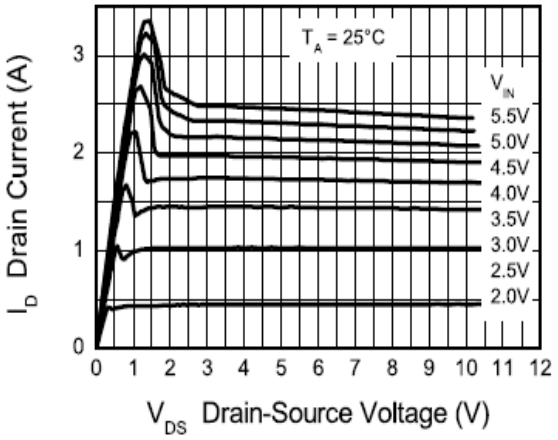
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	$V_{DS(AZ)}$	60	65	70	V	I_D = 10mA
Off-State Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 12V, V_{IN} = 0V
		—	—	2		V_{DS} = 36V, V_{IN} = 0V
Input Threshold Voltage	$V_{IN(th)}$	0.7	1	1.5	V	V_{DS} = V_{GS}, I_D = 1mA
Input Current	I_{IN}	—	60	100	µA	V_{IN} = +3V
		—	120	200		V_{IN} = +5V
Input Current while Over-Temperature Active	—	—	—	300	µA	V_{IN} = +5V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	—	400	600	mΩ	V_{IN} = +3V, I_D = 1A
		—	350	500		V_{IN} = +5V, I_D = 1A
Continuous Drain Current (Notes 5)	I_D	0.9	—	—	A	V_{IN} = 3V; T_A = +25°C
		1.0	—	—		V_{IN} = 5V; T_A = +25°C
Continuous Drain Current (Note 5)		1.1	—	—		V_{IN} = 3V; T_A = +25°C
		1.2	—	—		V_{IN} = 5V; T_A = +25°C
Current Limit (Note 8)	$I_{D(LIM)}$	0.7	1.7	—	A	V_{IN} = +3V
		1	2.2	—		V_{IN} = +5V
Dynamic Characteristics						
Turn On Delay Time	$t_{d(on)}$	—	5	—	µs	V_{DD} = 12V, I_D = 0.5A, V_{GS} = 5V
Rise Time	t_r	—	10	—	µs	
Turn Off Delay Time	$t_{d(off)}$	—	45	—	µs	
Fall Time	f_f	—	15	—	µs	
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 9)	T_{JT}	+150	+175	—	°C	—
Thermal Hysteresis (Note 9)	f_f	—	+10	—	°C	—

Notes: 8. The drain current is restricted only when the device is in saturation (see graph "Typical Output Characteristic"). This allows the device to be used in the on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

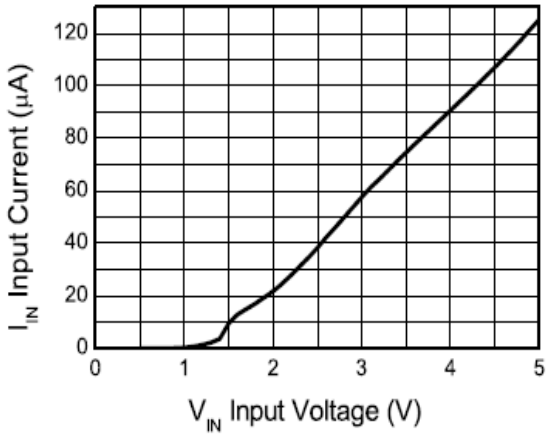
9. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

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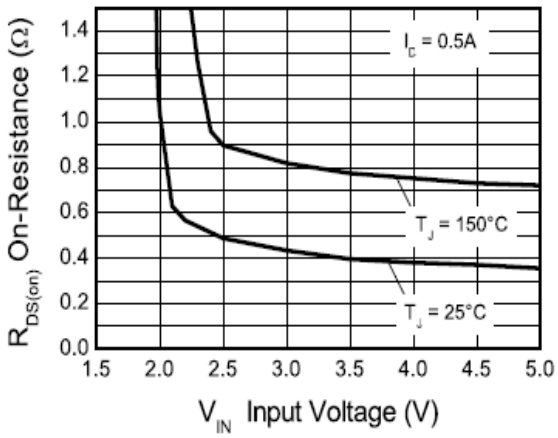
Typical Characteristics



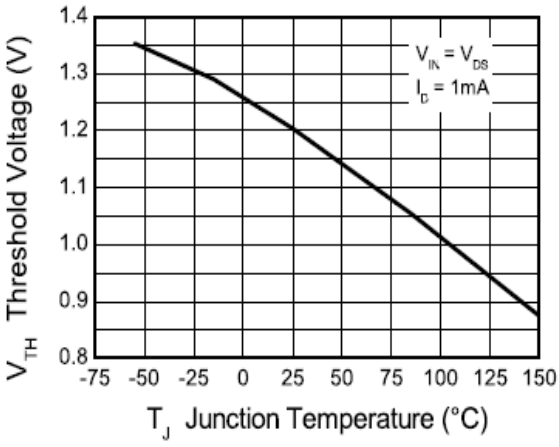
Typical Output Characteristic



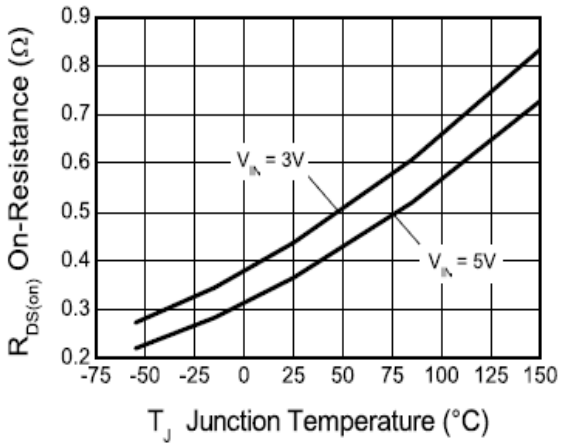
Input Current vs Input Voltage



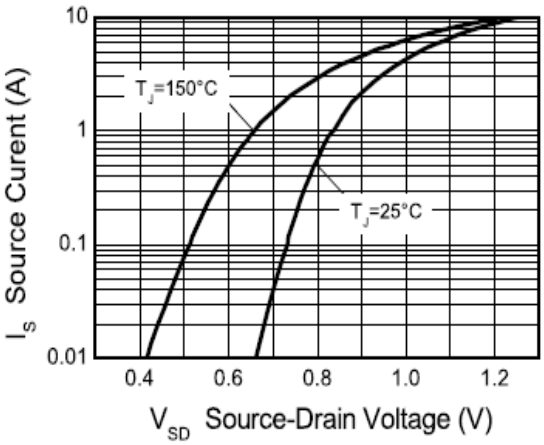
On-Resistance vs Input Voltage



Threshold Voltage vs Temperature



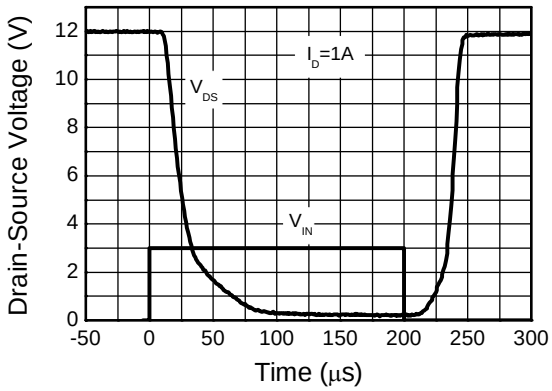
On-Resistance vs Temperature



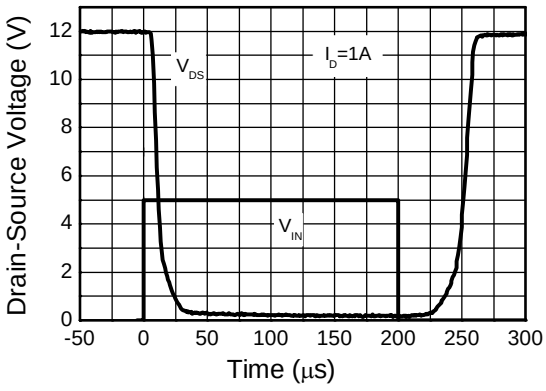
Reverse Diode Characteristic

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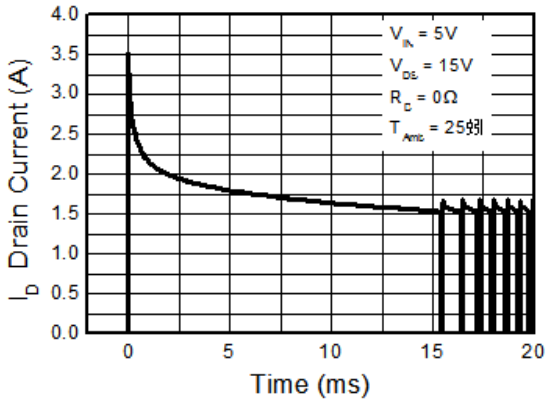
Typical Characteristics (Continued)



Switching Speed



Switching Speed



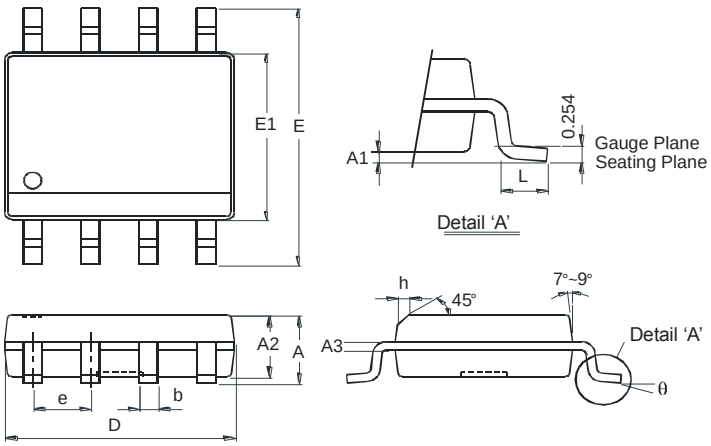
Typical Short Circuit Protection

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Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SO-8

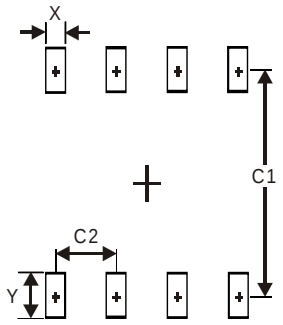


SO-8		
Dim	**Min**	**Max**
A	—	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	—	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SO-8



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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